MC74VHC1G09

2-Input AND Gate with Open Drain Output

The MC74VHC1G09 is an advanced high speed CMOS 2–input AND gate with open drain output fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including an open drain output which provides the capability to set output switching level. This allows the MC74VHC1G09 to be used to interface 5.0 V circuits to circuits of any voltage between V_{CC} and 7.0 V using an external resistor and power supply.

The MC74VHC1G09 input structure provides protection when voltages up to 7.0 V are applied, regardless of the supply voltage.

Features

- High Speed: t_{PD} = 4.3 ns (Typ) at V_{CC} = 5.0 V
- Low Internal Power Dissipation: I_{CC} = 1 μA (Max) at T_A = 25°C
- Power Down Protection Provided on Inputs
- Pin and Function Compatible with Other Standard Logic Families
- Chip Complexity: FETs = 62; Equivalent Gates = 16
- Pb−Free Packages are Available

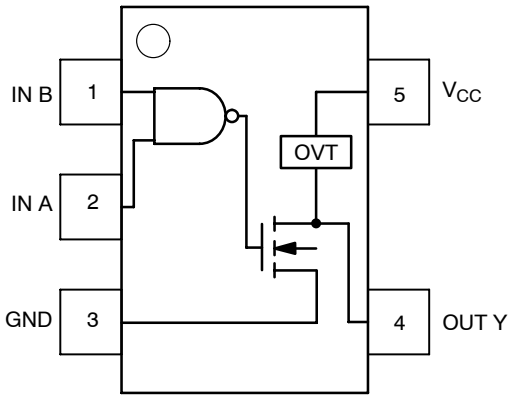

Figure 1. Pinout (Top View)

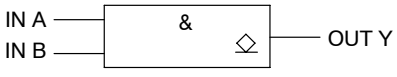

Figure 2. Logic Symbol

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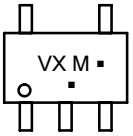
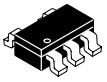
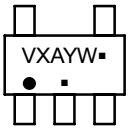
MARKING DIAGRAMS

SC−88A / SOT−353 / SC−70
DF SUFFIX
CASE 419A





TSOP−5 / SOT−23 / SC−59
DT SUFFIX
CASE 483



M = Date Code
A = Assembly Location
Y = Year
W = Work Week
▪ = Pb−Free Package
(Note: Microdot may be in either location)

PIN ASSIGNMENT	
1	IN B
2	IN A
3	GND
4	OUT Y
5	V_{CC}

FUNCTION TABLE

Inputs		Output
A	**B**	**Y**
L	L	L
L	H	L
H	L	L
H	H	Z

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MAXIMUM RATINGS

Symbol	Characteristics		Value	Unit
V_{CC}	DC Supply Voltage		−0.5 to +7.0	V
V_{IN}	DC Input Voltage		−0.5 to +7.0	V
V_{OUT}	DC Output Voltage		−0.5 to 7.0	V
I_{IK}	Input Diode Current		−20	mA
I_{OK}	Output Diode Current		+20	mA
I_{OUT}	DC Output Current, per Pin		+25	mA
I_{CC}	DC Supply Current, V_{CC} and GND		+50	mA
P_D	Power dissipation in still air	SC−88A, TSOP−5	200	mW
θ_{JA}	Thermal resistance	SC−88A, TSOP−5	333	°C/W
T_L	Lead temperature, 1 mm from case for 10 s		260	°C
T_J	Junction temperature under bias		+150	°C
T_{stg}	Storage temperature		−65 to +150	°C
MSL	Moisture Sensitivity		Level 1	
F_R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V−0 @ 0.125 in	
V_{ESD}	ESD Withstand Voltage	Human Body Model (Note 1) Machine Model (Note 2) Charged Device Model (Note 3)	> 2000 > 200 N/A	V
$I_{Latchup}$	Latchup Performance	Above V_{CC} and Below GND at 125°C (Note 4)	±500	mA

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Tested to EIA/JESD22−A114−A
2. Tested to EIA/JESD22−A115−A
3. Tested to JESD22−C101−A
4. Tested to EIA/JESD78

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics		Min	Max	Unit
V_{CC}	DC Supply Voltage		2.0	5.5	V
V_{IN}	DC Input Voltage		0.0	5.5	V
V_{OUT}	DC Output Voltage		0.0	7.0	V
T_A	Operating Temperature Range		−55	+125	°C
t_r , t_f	Input Rise and Fall Time	V_{CC} = 3.3 V ± 0.3 V V_{CC} = 5.0 V ± 0.5 V	0 0	100 20	ns/V

Device Junction Temperature versus Time to 0.1% Bond Failures

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

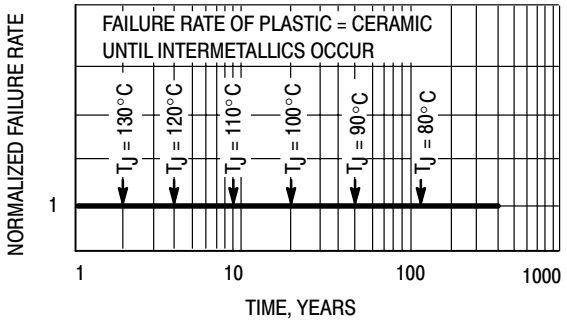


Figure 3. Failure Rate vs. Time Junction Temperature

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V_{CC} (V)	T_A = 25°C			$T_A \le$ 85°C		−55 ≤ $T_A \le$ 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V_{IH}	Minimum High−Level Input Voltage		2.0 3.0 4.5 5.5	1.5 2.1 3.15 3.85			1.5 2.1 3.15 3.85		1.5 2.1 3.15 3.85		V
V_{IL}	Maximum Low−Level Input Voltage		2.0 3.0 4.5 5.5			0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65	V
V_{OL}	Maximum Low−Level Output Voltage $V_{IN} = V_{IH}$ or V_{IL}	$V_{IN} = V_{IH}$ or V_{IL} I_{OL} = 50 μA	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		$V_{IN} = V_{IH}$ or V_{IL} I_{OL} = 4 mA I_{OL} = 8 mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	V
I_{IN}	Maximum Input Leakage Current	V_{IN} = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μA
I_{CC}	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			1.0		20		40	μA
I_{OFF}	Power Off−Output Leakage Current	V_{OUT} = 5.5 V V_{IN} = 5.5 V	0			0.25		2.5		5	μA

AC ELECTRICAL CHARACTERISTICS C_{load} = 50 pF, Input $t_r = t_f$ = 3.0 ns

Symbol	Parameter	Test Conditions	T_A = 25°C			$T_A \le$ 85°C		−55 ≤ $T_A \le$ 125°C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t_{PZL}	Maximum Output Enable Time, Input A or B to Y	V_{CC} = 3.3 ± 0.3 V C_L = 15 pF $R_L = R_I$ = 500 Ω C_L = 50 pF		6.2 8.7	8.8 12.3		10.5 14.0		12.5 16.5	ns
		V_{CC} = 5.0 ± 0.5 V C_L = 15 pF $R_L = R_I$ = 500 Ω C_L = 50 pF		4.3 5.8	5.9 7.9		7.0 9.0		9.0 11.0	
t_{PLZ}	Maximum Output Disable Time	V_{CC} = 3.3 ± 0.3 V C_L = 50 pF $R_L = R_I$ = 500 Ω		8.7	12.3		14.0		16.5	ns
		V_{CC} = 5.0 ± 0.5 V C_L = 50 pF $R_L = R_I$ = 500 Ω		5.8	7.9		9.0		11.0	
C_{IN}	Maximum Input Capacitance			6.0	10		10		10	pF

		Typical @ 25°C, V_{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Note 5)	18	pF

5. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no−load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

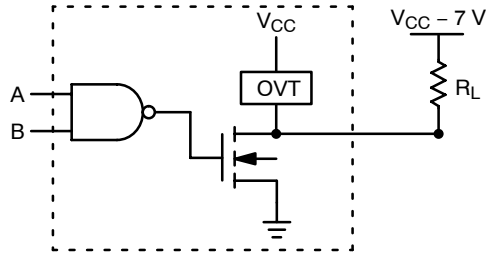


Figure 4. Output Voltage Mismatch Application

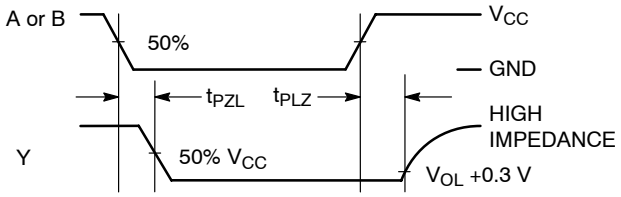
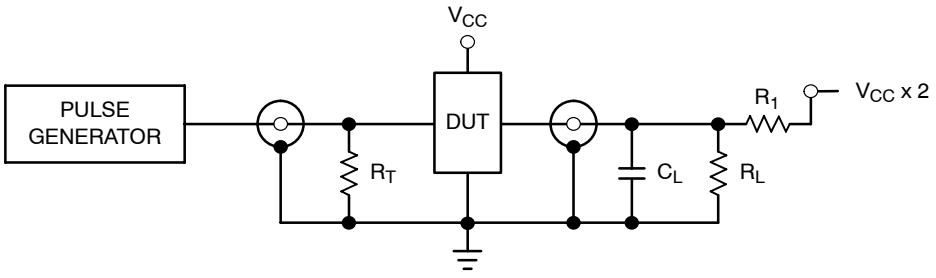


Figure 5. Switching Waveforms



C_L = 50 pF equivalent (Includes jig and probe capacitance)
$R_L = R_1$ = 500 Ω or equivalent
$R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)

Figure 6. Test Circuit

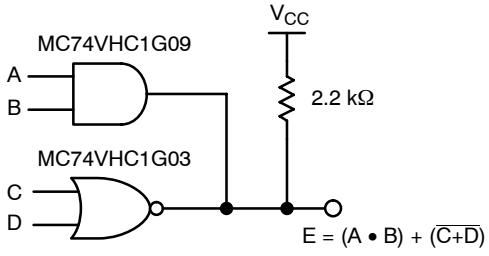


Figure 7. Complex Boolean Functions

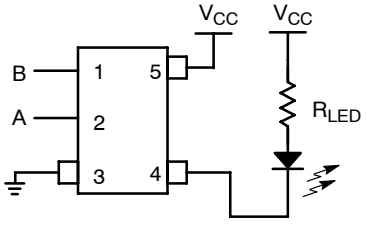


Figure 8. LED Driver

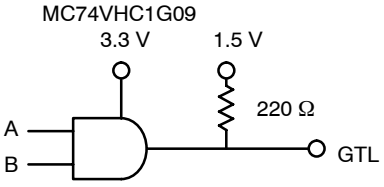


Figure 9. GTL Driver

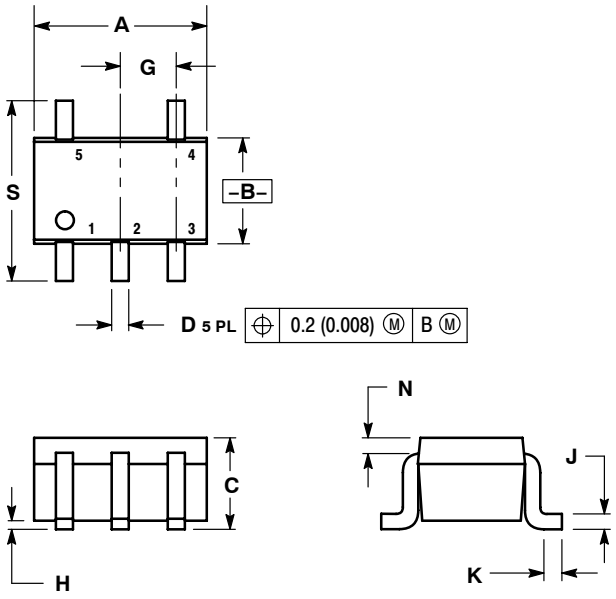
DEVICE ORDERING INFORMATION

Device Order Number	Package Type	Tape and Reel Size†
MC74VHC1G09DFT1	SC70–5 / SC–88A / SOT–353	178 mm (7”) 3000 Unit
MC74VHC1G09DFT1G	SC70–5 / SC–88A / SOT–353 (Pb–Free)	178 mm (7”) 3000 Unit
MC74VHC1G09DFT2	SC70–5 / SC–88A / SOT–353	178 mm (7”) 3000 Unit
MC74VHC1G09DFT2G	SC70–5 / SC–88A / SOT–353 (Pb–Free)	178 mm (7”) 3000 Unit
MC74VHC1G09DTT1	SOT23–5 / TSSOP–5 / SC59–5	178 mm (7”) 3000 Unit
MC74VHC1G09DTT1G	SOT23–5 / TSSOP–5 / SC59–5 (Pb–Free)	178 mm (7”) 3000 Unit

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

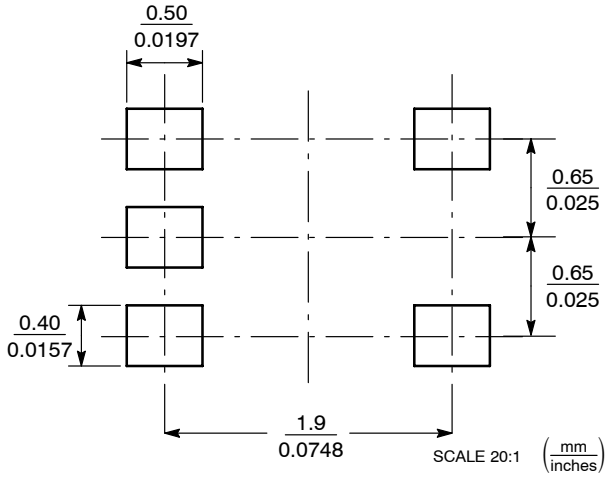
SC−88A, SOT−353, SC−70
CASE 419A−02
ISSUE J



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419A−01 OBSOLETE. NEW STANDARD 419A−02.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20

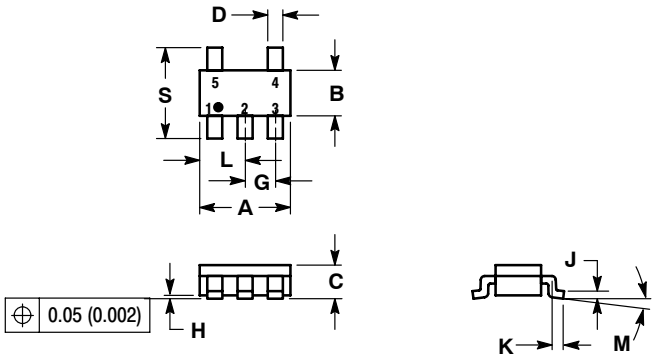
SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

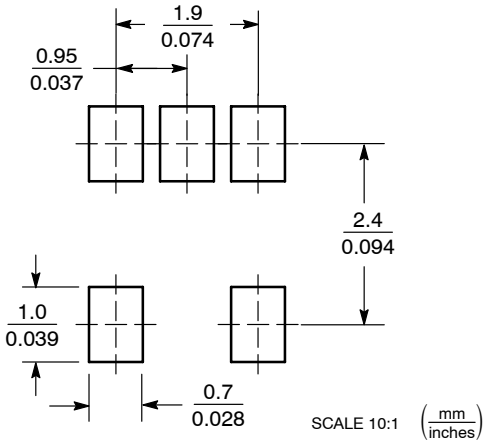
TSOP−5/SOT−23/SC−59
CASE 483−02
ISSUE D



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. A AND B DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	2.90	3.10	0.1142	0.1220
B	1.30	1.70	0.0512	0.0669
C	0.90	1.10	0.0354	0.0433
D	0.25	0.50	0.0098	0.0197
G	0.85	1.05	0.0335	0.0413
H	0.013	0.100	0.0005	0.0040
J	0.10	0.26	0.0040	0.0102
K	0.20	0.60	0.0079	0.0236
L	1.25	1.55	0.0493	0.0610
M	0 °	10 °	0 °	10 °
S	2.50	3.00	0.0985	0.1181

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

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